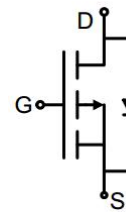# P-Channel Enhancement Mode Power MOSFET

Description

The G07P04S-BQ uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.
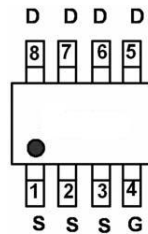
General Features

- V_{DS} -40V
- I_D (at V_{GS} = -10V)   -7A
- $R_{DS(ON)}$ (at V_{GS} = -10V)   <   18mΩ
- $R_{DS(ON)}$ (at V_{GS} = -4.5V)   <   22mΩ
- 100% Avalanche Tested
- RoHS Compliant

Application

- Power switch
- DC/DC converters

Schematic diagram

pin assignment

SOP-8

Ordering Information

Device	Package	Marking	Packaging
G07P04S-BQ	SOP-8	G07P04	4000pcs/Reel

Absolute Maximum Ratings T_C = 25ºC, unless otherwise noted

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	-40	V
Continuous Drain Current		I_D	-7	A
Pulsed Drain Current	(note1)	I_{DM}	-28	A
Gate-Source Voltage		V_{GS}	±20	V
Power Dissipation		P_D	2.5	W
Operating Junction and Storage Temperature Range		T_J, T_{stg}	-55 To 150	ºC

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	ºC/W

Specifications T_J = 25ºC, unless otherwise noted

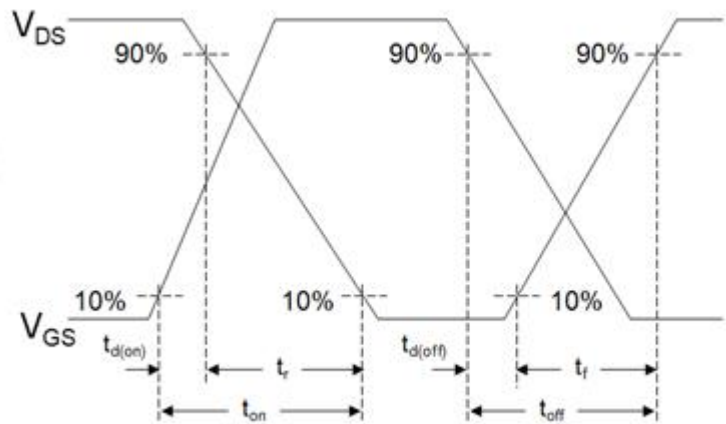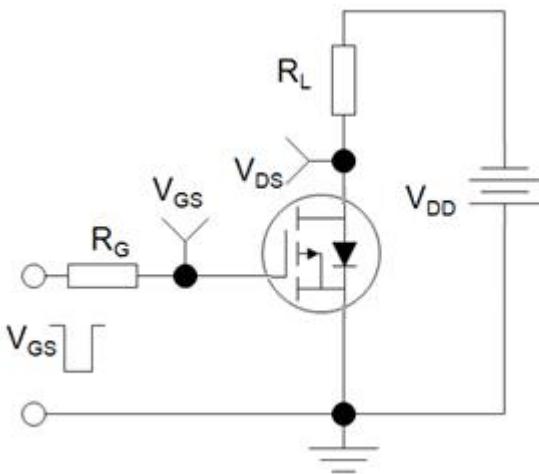| Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = -250µA	-40	--	--	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = -40V, V_{GS} = 0V	--	--	-1	µA
Gate-Source Leakage	I_{GSS}	V_{GS} = $\pm$20V	--	--	$\pm$100	nA
Gate-Source Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = -250µA	-1	-1.5	-2.5	V
Drain-Source On-Resistance	$R_{DS(on)}$	V_{GS} = -10V, I_D = -7A	--	14	18	mΩ
		V_{GS} = -4.5V, I_D = -7A	--	18	22	
Forward Transconductance	g_{FS}	V_{DS} = -10V,I_D = -7A	--	17	--	S
Dynamic Parameters						
Input Capacitance	C_{iss}	V_{GS} = 0V, V_{DS} = -20V, f = 1.0MHz	--	1750	--	pF
Output Capacitance	C_{oss}		--	215	--	
Reverse Transfer Capacitance	C_{rss}		--	180	--	
Total Gate Charge	Q_g	V_{DD} = -20V, I_D = -7A, V_{GS} = -10V	--	31	--	nC
Gate-Source Charge	Q_{gs}		--	7.6	--	
Gate-Drain Charge	Q_{gd}		--	6.2	--	
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = -20V, I_D = -7A, R_G = 3Ω	--	18	--	ns
Turn-on Rise Time	t_r		--	10	--	
Turn-off Delay Time	$t_{d(off)}$		--	38	--	
Turn-off Fall Time	t_f		--	24	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I_S	T_C = 25ºC	--	--	-7	A
Body Diode Voltage	V_{SD}	T_J = 25ºC, I_{SD} = -7A, V_{GS} = 0V	--	--	-1.2	V
Reverse Recovery Charge	Q_{rr}	I_F = -7A, V_{GS} = 0V di/dt=-100A/us	--	30	--	nC
Reverse Recovery Time	T_{rr}		--	32	--	ns

Notes

1. Repetitive Rating: Pulse width limited by maximum junction temperature

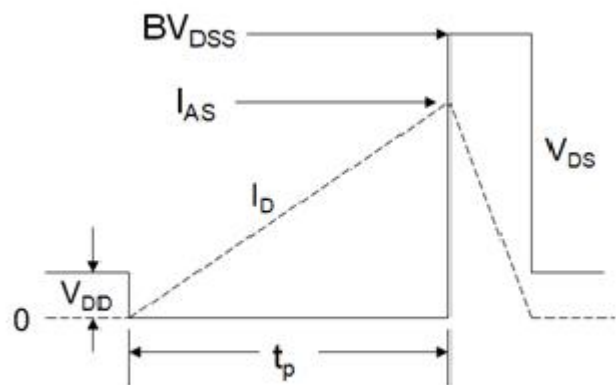2. Identical low side and high side switch with identical R_G

Gate Charge Test Circuit

Switch Time Test Circuit

EAS Test Circuit

Typical Characteristics T_J = 25°C, unless otherwise noted
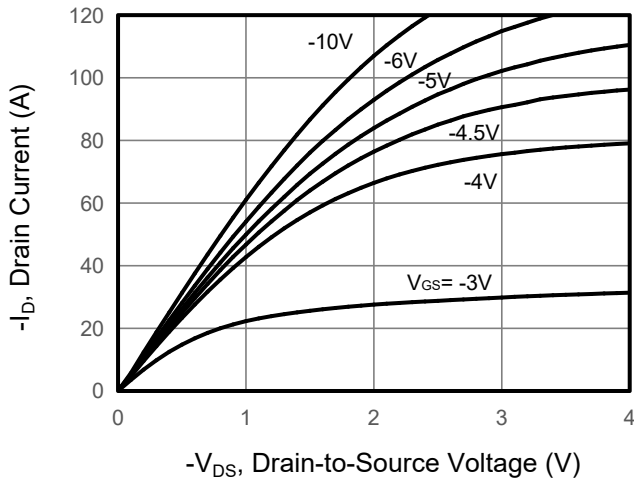
Figure 1. Output Characteristics
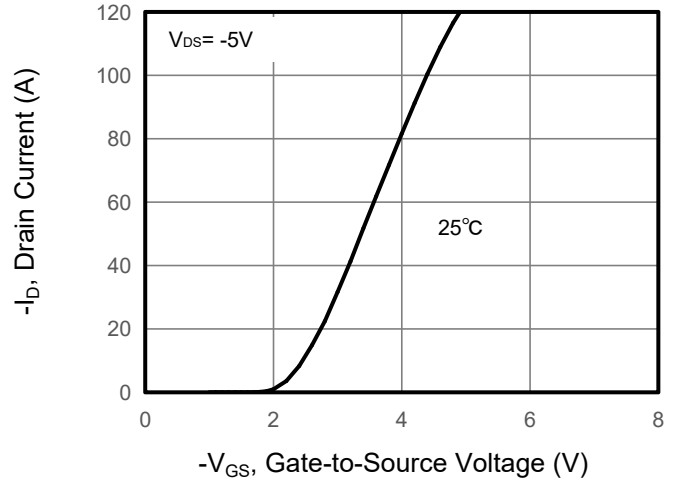

Figure 2. Transfer Characteristics

Figure 3. Drain Source On Resistance
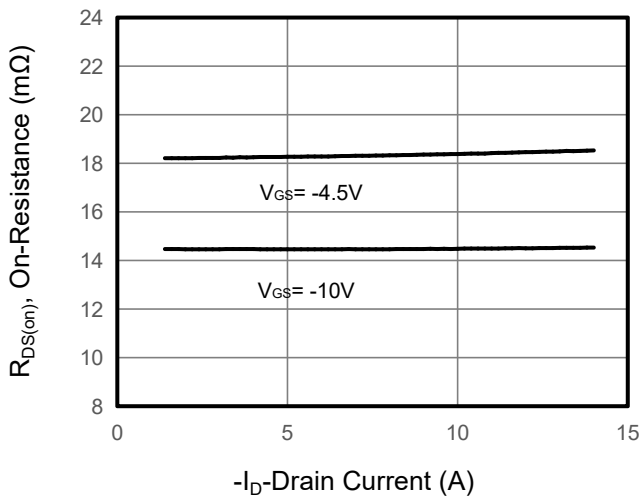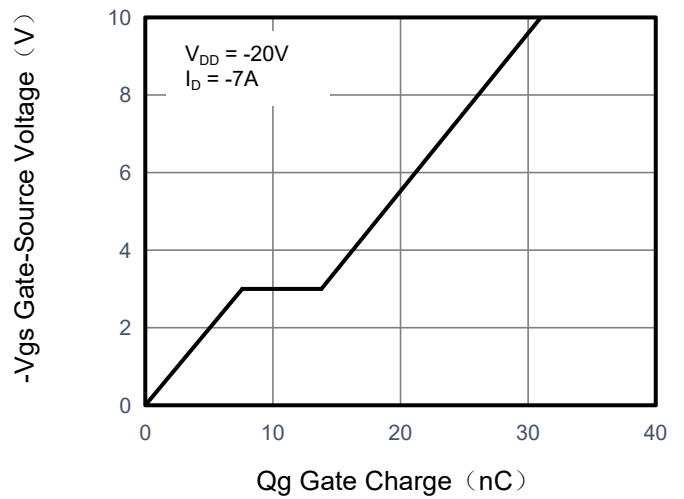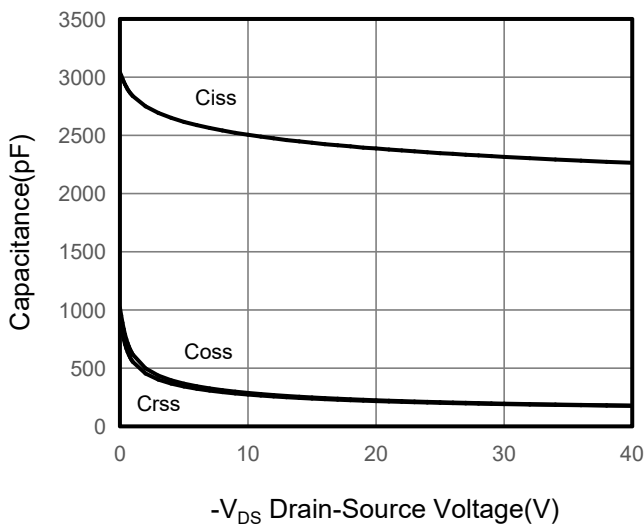

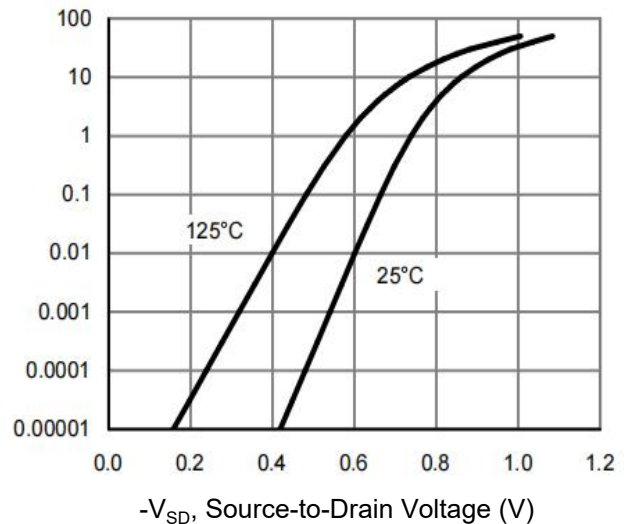**Figure 4. Gate Charge**

Figure 5. Capacitance

Figure 6. Source-Drain Diode Forward

Typical Characteristics T_J = 25°C, unless otherwise noted
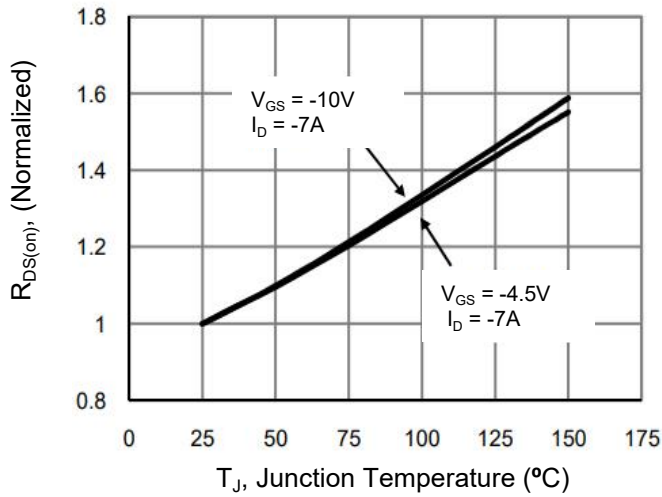
Figure 7. Drain-Source On-Resistance

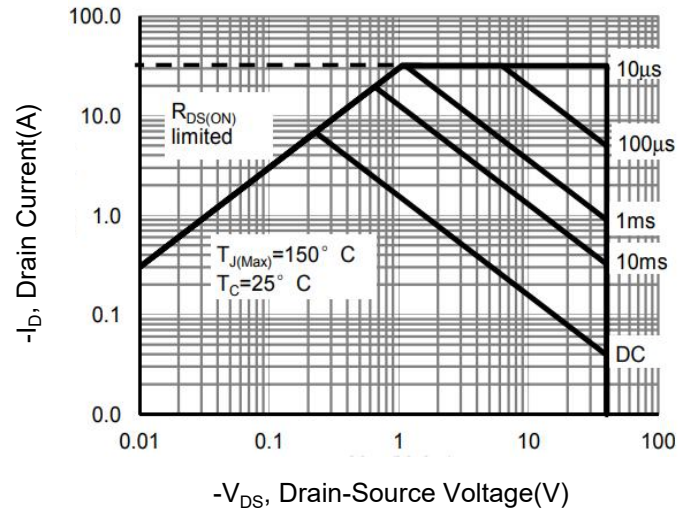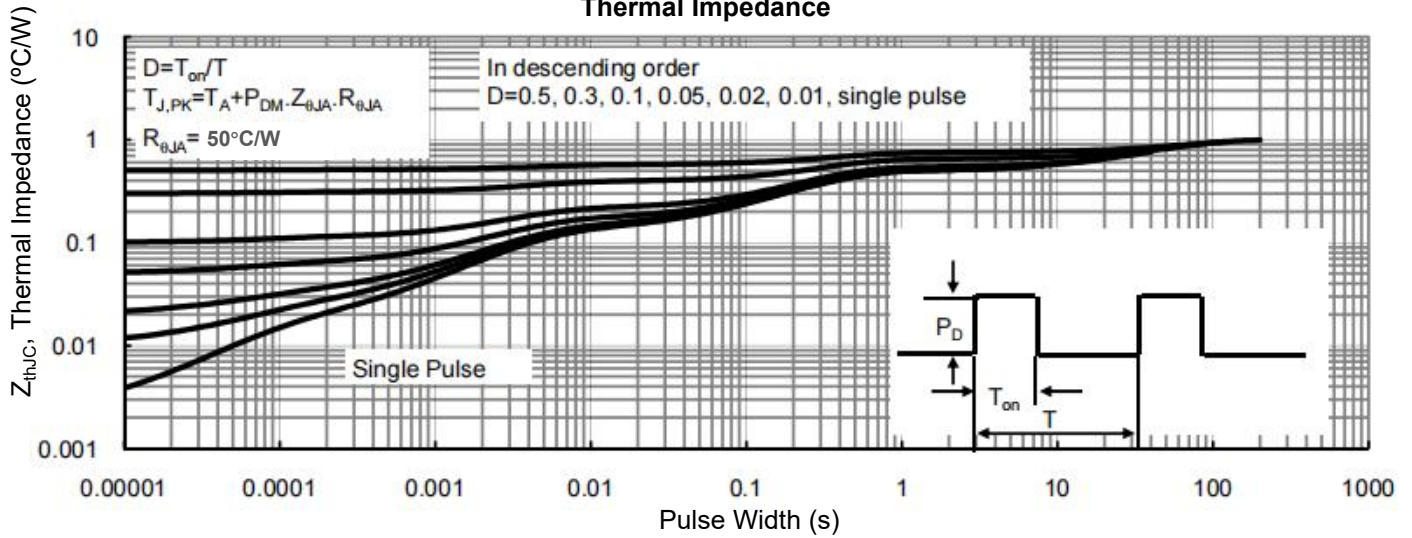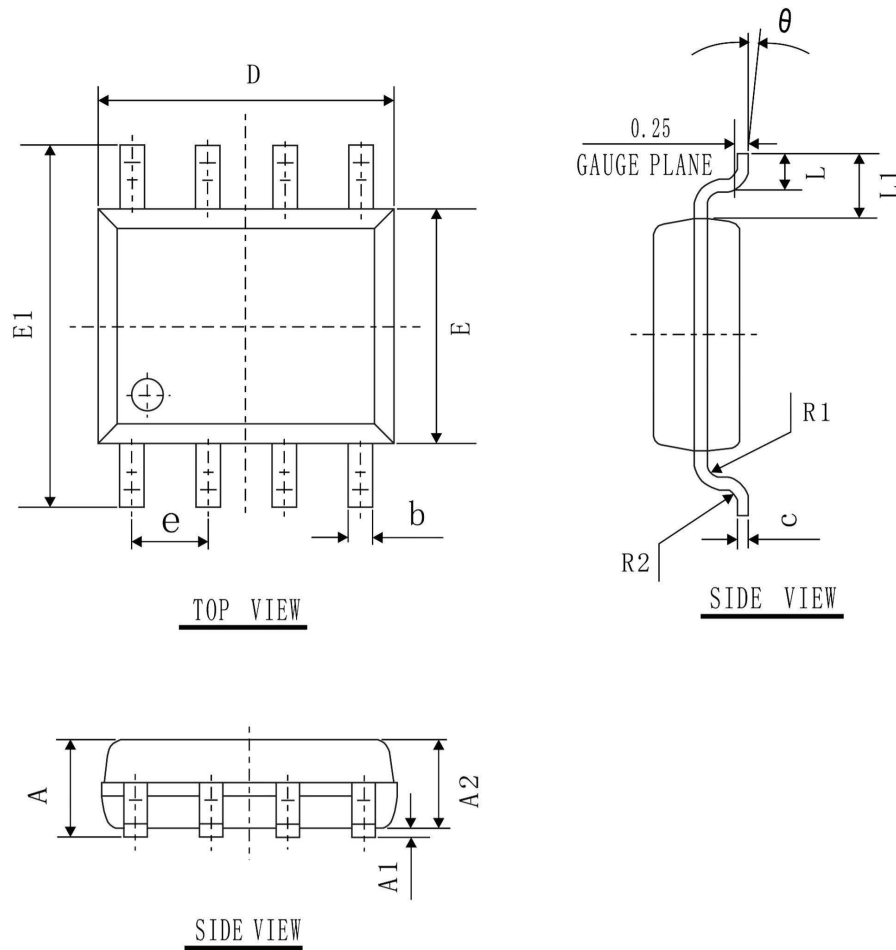**Figure 10. Safe Operation Area**

Figure 9. Normalized Maximum Transient Thermal Impedance

SOP-8 Package Information

TOP VIEW

SIDE VIEW

SIDE VIEW

COMMON DIMENSIONS
(UNITS OF MEASURE=mm)

SYMBOL	MIN	NOM	MAX
A	1.40	1.60	1.80
A1	0.05	0.15	0.25
A2	1.35	1.45	1.55
b	0.30	0.40	0.50
c	0.153	0.203	0.253
D	4.80	4.90	5.00
E	3.80	3.90	4.00
E1	5.80	6.00	6.20
L	0.45	0.70	1.00
θ	2°	4°	6°
L1	1.04 REF		
e	1.27 BSC		
R1	0.07 TYP		
R2	0.07 TYP		